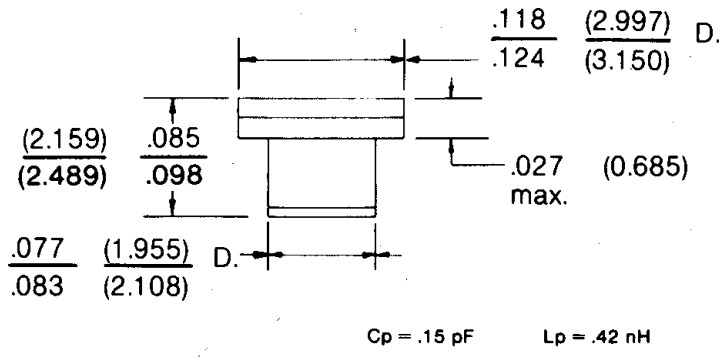
SILICON ABRUPT JUNCTION TUNING VARACTOR

DESCRIPTION:

The **AT6017-10** is an Epitaxial Silicon Abrupt Junction Microwave Tuning Varactor. This Device is Passivated With Silicon Dioxide Which Results in Very Low Leakage Current. The Capacitance Voltage Relationship Closley Approximates Square Law (n = 0.5).

PACKAGE STYLE 10



MAXIMUM RATINGS

I_C	100 mA
V_{CE}	60 V
P_{DISS}	250 mW @ T_C = 25 °C
T_J	-65 °C to +150 °C
T_{STG}	-65 °C to +150 °C

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS		MINIMUM	TYPICAL	MAXIMUM	UNITS
V_B	I_R = 10 µA		60			V
C_T	V_R = 4.0 V	f = 1.0 MHz	19.80	22.00	24.20	pF
ΔC_T	C_T= 0 V / C_T = 8.0 V	f = 1.0 MHz	7.2			RATIO
Q	V_R = 4.0 V	f = 50 MHz	800			---
T_C	V_R = 4.0 V				300	Ppm/^{O}C